MMBT123S

1A NPN SURFACE MOUNT TRANSISTOR

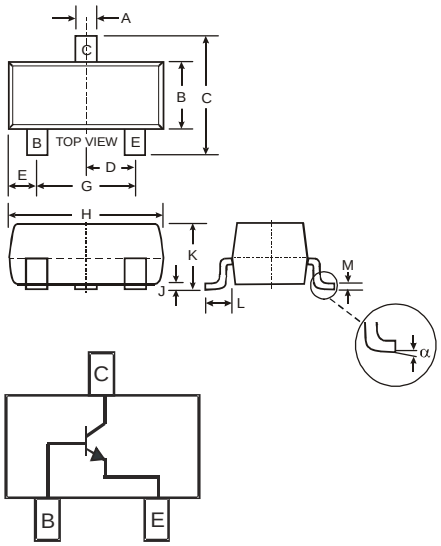
Please click here to visit our online spice models database.

Features

- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- **Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 2 and 4)**

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)



SOT-23		
Dim	**Min**	**Max**
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
α	0°	8°
All Dimensions in mm		

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	45	V
Collector-Emitter Voltage	V_{CEO}	18	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current - Continuous	I_C	1	A
Power Dissipation (Note 1)	P_D	300	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	417	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 3)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	45	—	V	I_C = 100μA, I_E = 0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	18	—	V	I_C = 1mA, I_B = 0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5	—	V	I_E = 100μA, I_C = 0
Collector Cutoff Current	I_{CBO}	—	1	μA	V_{CB} = 40V, I_E = 0
Emitter Cutoff Current	I_{EBO}	—	1	μA	V_{EB} = 4V, I_C = 0
ON CHARACTERISTICS (Note 3)					
DC Current Gain	h_{FE}	150	800	—	I_C = 100mA, V_{CE} = 1V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	0.5	V	I_C = 300mA, I_B = 30mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	—	8	pF	V_{CB} = 10V, f = 1.0MHz, I_E = 0
Current Gain-Bandwidth Product	f_T	100	—	MHz	V_{CB} = 10V, I_E = 50mA, f = 100MHz

Notes:
1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
2. No purposefully added lead. Halogen and Antimony Free.
3. Short duration pulse test used to minimize self-heating effect.
4. Product manufactured with Data Code V9 (week 33, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V9 are built with Non-Green Molding Compound and may contain Halogens or Sb_2O_3 Fire Retardants.

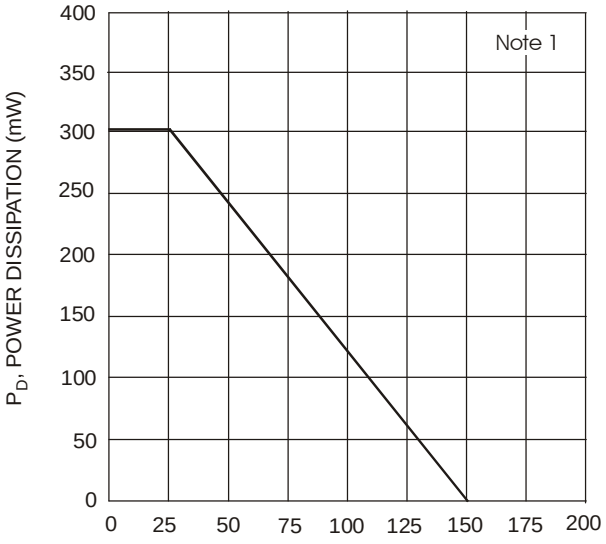


Fig. 1, Max Power Dissipation vs Ambient Temperature

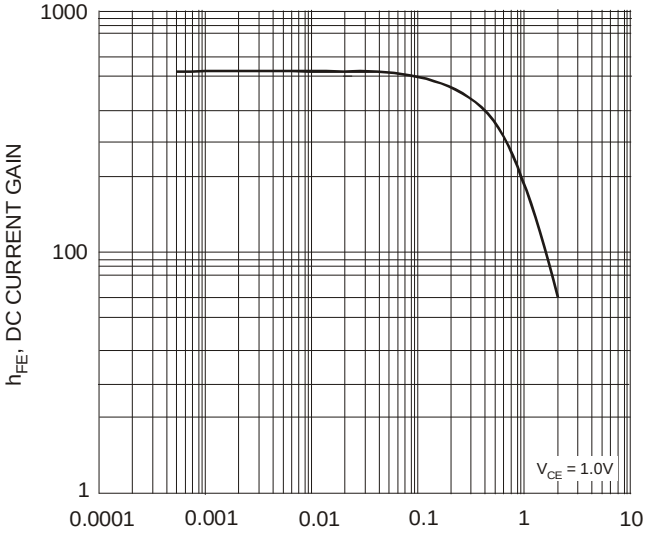


Fig. 2, Typical DC Current Gain vs Collector Current

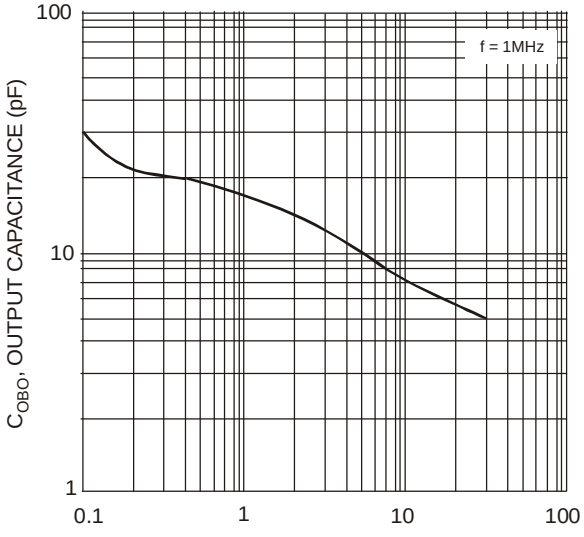


Fig. 3, Output Capacitance vs. Collector-Base Voltage

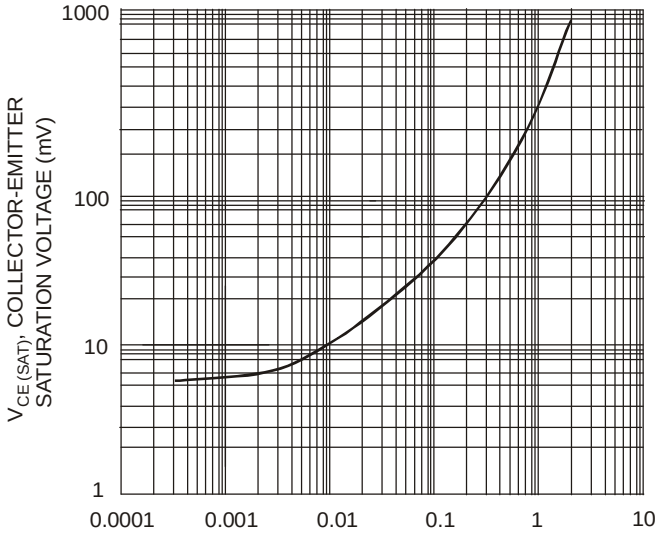


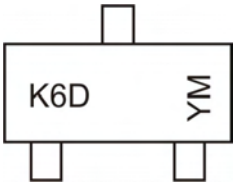
Fig. 4, Collector Saturation Voltage vs Collector Current

Ordering Information (Note 5)

Device	Packaging	Shipping
MMBT123S-7-F	SOT-23	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



K6D = Product Type Marking Code
YM = Date Code Marking
Y = Year ex: T = 2006
M = Month ex: 9 = September

Date Code Key

Year	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	N	P	R	S	T	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

单击下面可查看定价，库存，交付和生命周期等信息

>>Diodes Incorporated(达迩科技（美台）)